

TOSHIBA FIELD EFFECT TRANSISTOR SILICON N CHANNEL MOS TYPE (π -MOSV)

2SK2544

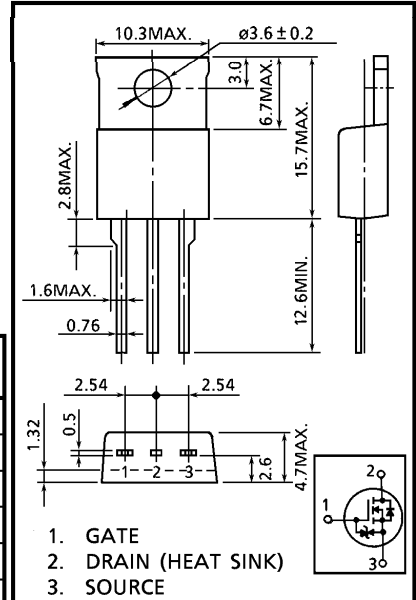
HIGH SPEED, HIGH VOLTAGE SWITCHING APPLICATIONS
SWITCHING REGURATOR APPLICATIONS

INDUSTRIAL APPLICATIONS
Unit in mm

- Low Drain-Source ON Resistance : $R_{DS(ON)} = 0.9\Omega$ (Typ.)
- High Forward Transfer Admittance : $|Y_{fs}| = 5.5S$ (Typ.)
- Low Leakage Current : $I_{DSS} = 100\mu A$ (Max.) ($V_{DS} = 600V$)
- Enhancement-Mode : $V_{th} = 2.0 \sim 4.0V$ ($V_{DS} = 10V, I_D = 1mA$)

MAXIMUM RATINGS ($T_a = 25^\circ C$)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Drain-Source Voltage	V_{DSS}	600	V
Drain-Gate Voltage ($R_{GS} = 20k\Omega$)	V_{DGR}	600	V
Gate-Source Voltage	V_{GSS}	± 30	V
Drain Current	DC	I_D	6 A
	Pulse	I_{DP}	24 A
Drain Power Dissipation ($T_c = 25^\circ C$)	P_D	80	W
Single Pulse Avalanche Energy**	E_{AS}	345	mJ
Avalanche Current	I_{AR}	6	A
Repetitive Avalanche Energy*	E_{AR}	8	mJ
Channel Temperature	T_{ch}	150	$^\circ C$
Storage Temperature Range	T_{stg}	$-55 \sim 150$	$^\circ C$



JEDEC TO-220AB

EIAJ SC-46

TOSHIBA 2-10P1B

Weight : 2.0g

Thermal Characteristics

CHARACTERISTIC	SYMBOL	MAX.	UNIT
Thermal Resistance, Channel to Case	$R_{th(ch-c)}$	1.56	$^\circ C/W$
Thermal Resistance, Channel to Ambient	$R_{th(ch-a)}$	83.3	$^\circ C/W$

Note ;

* Repetitive rating ; Pulse Width Limited by Max. junction temperature.

** $V_{DD} = 90V$, Starting $T_{ch} = 25^\circ C$, $L = 16.8mH$, $R_G = 25\Omega$, $I_{AR} = 6A$

**This transistor is an electrostatic sensitive device.
Please handle with caution.**

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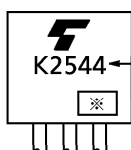
ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Gate Leakage Current		IGSS	VGS = ±25V, VDS = 0V	—	—	±10	μA
Gate-Source Breakdown Voltage		V (BR) GSS	IG = ±10μA, VDS = 0V	±30	—	—	V
Drain Cut-off Current		IDSS	VDS = 600V, VGS = 0V	—	—	100	μA
Drain-Source Breakdown Voltage		V (BR) DSS	ID = 10mA, VGS = 0V	600	—	—	V
Gate Threshold Voltage		Vth	VDS = 10V, ID = 1mA	2.0	—	4.0	V
Drain-Source ON Resistance		RDS (ON)	VGS = 10V, ID = 3A	—	0.9	1.25	Ω
Forward Transfer Admittance		Yfs	VDS = 10V, ID = 3A	2.0	5.5	—	S
Input Capacitance		Ciss	VDS = 10V, VGS = 0V, f = 1MHz	—	1300	—	pF
Reverse Transfer Capacitance		Crss		—	130	—	
Output Capacitance		Coss		—	400	—	
Switching Time	Rise Time	tr		—	25	—	ns
	Turn-on Time	ton		—	45	—	
	Fall Time	tf		—	40	—	
	Turn-off Time	t _{off}		VIN : tr, tf < 5ns, Duty ≤ 1%, tw = 10μs	—	150	
Total Gate Charge (Gate-Source Plus Gate-Drain)		Qg	VDD ≐ 400V, VGS = 10V, ID = 6A	—	30	—	nC
Gate-Source Charge		Qgs		—	18	—	
Gate-Drain ("Miller") Charge		Qgd		—	12	—	

SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Continuous Drain Reverse Current	IDR	—	—	—	6	A
Pulse Drain Reverse Current	IDRP	—	—	—	24	A
Diode Forward Voltage	VDSF	IDR = 6A, VGS = 0V	—	—	-1.7	V
Reverse Recovery Time	trr	IDR = 6A, VGS = 0V	—	1000	—	ns
Reverse Recovery Charge	Qrr	dIDR / dt = 100A / μs	—	7	—	μC

MARKING

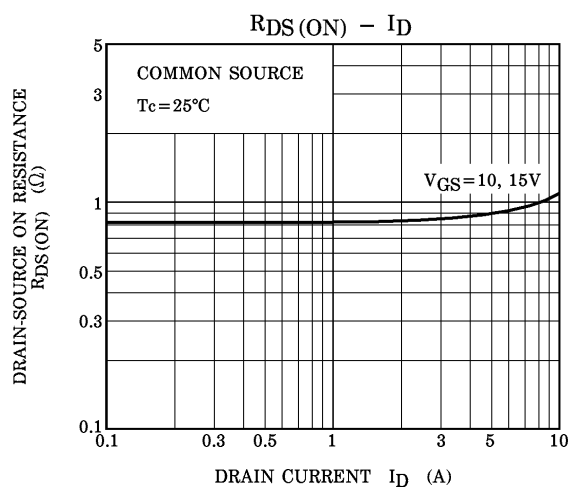
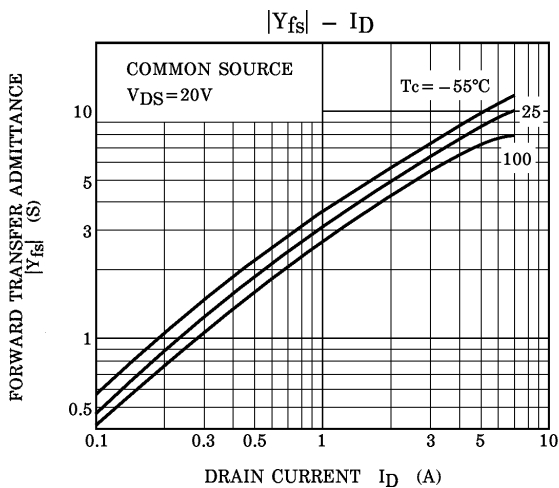
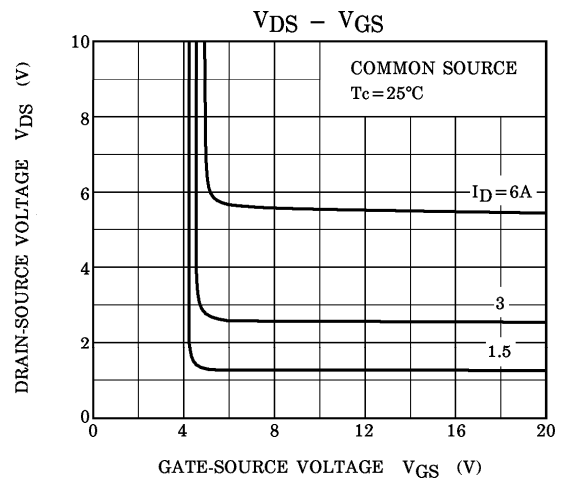
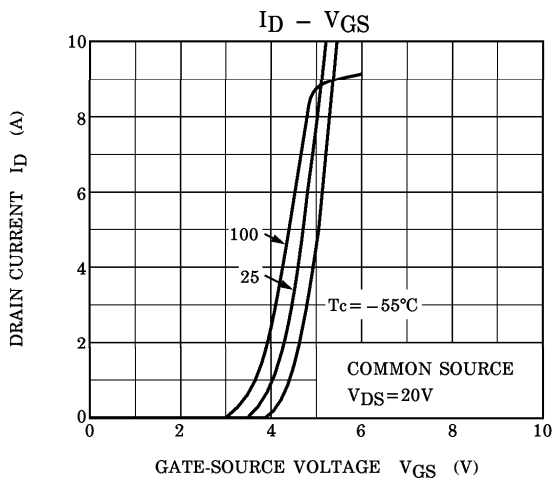
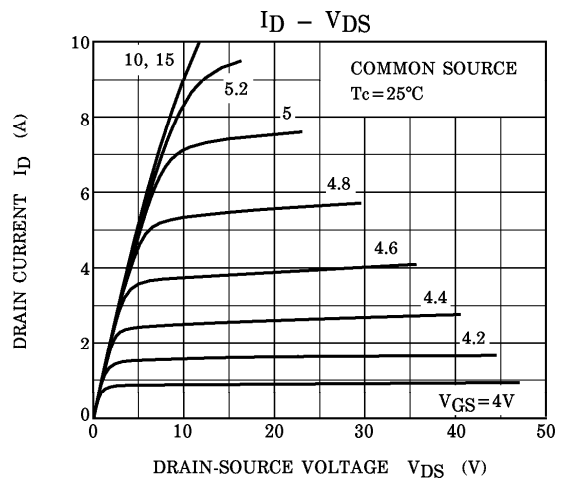
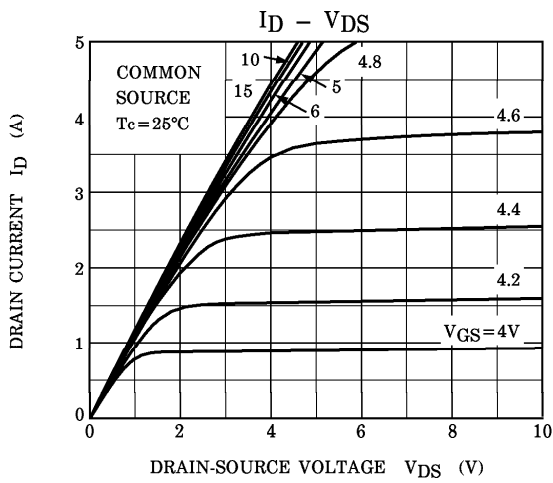


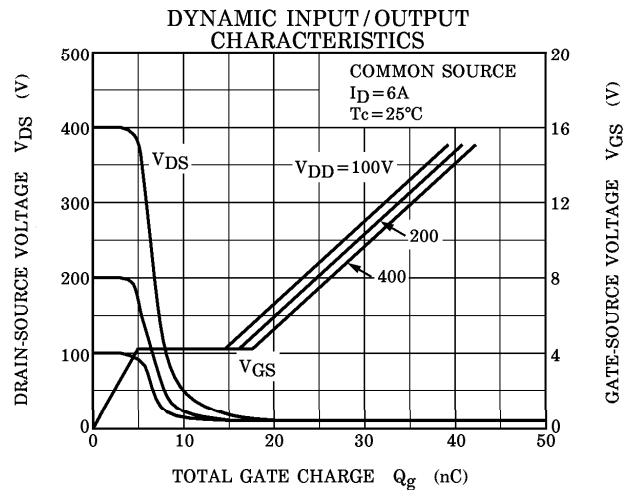
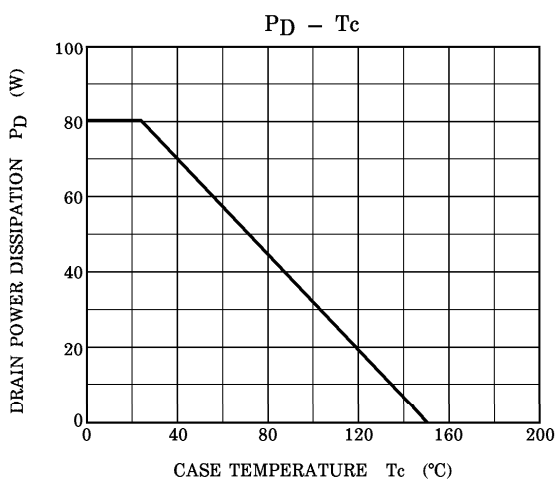
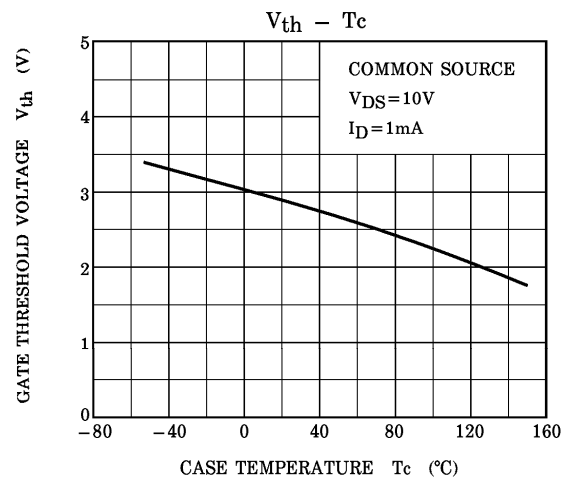
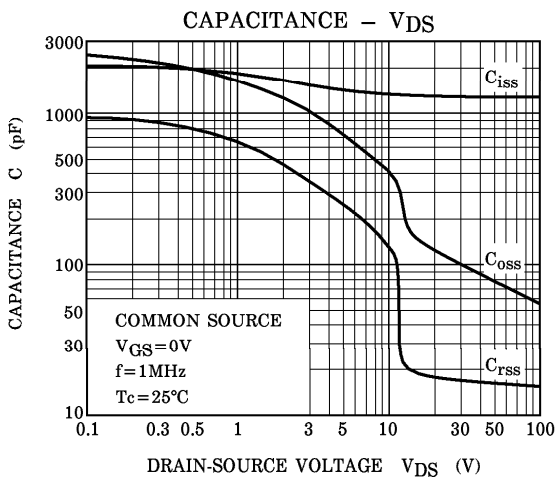
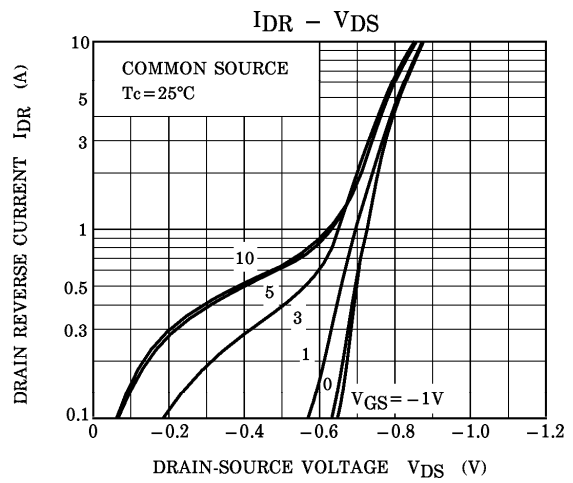
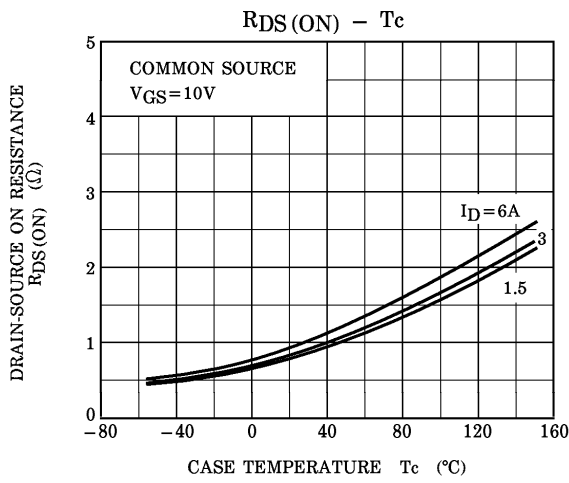
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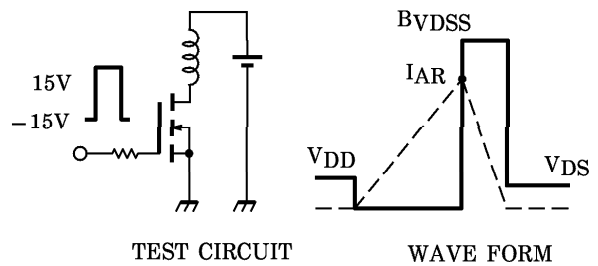
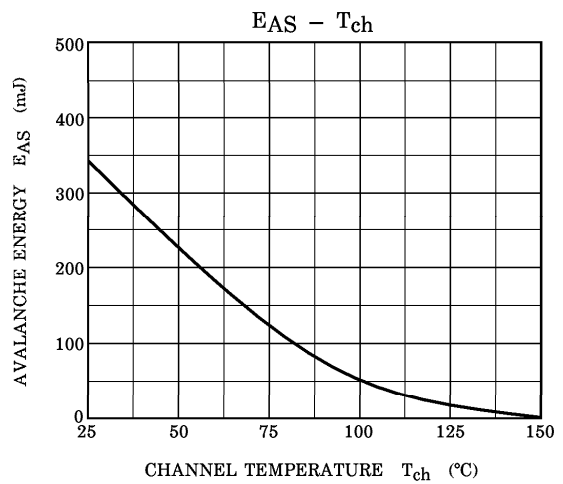
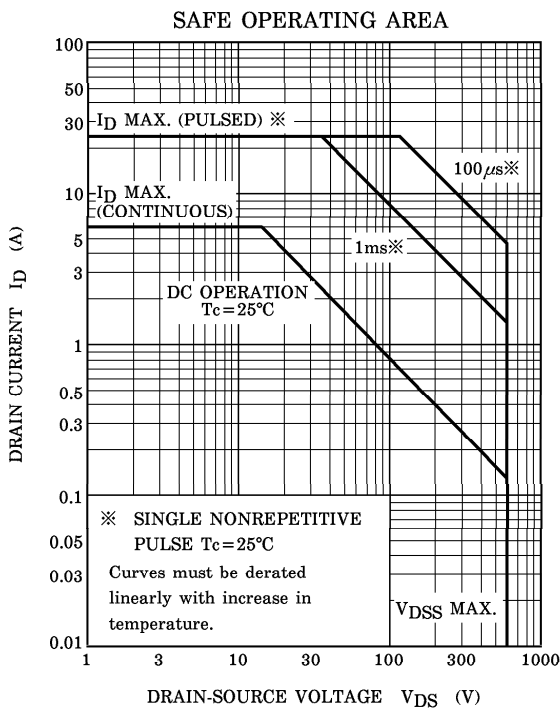
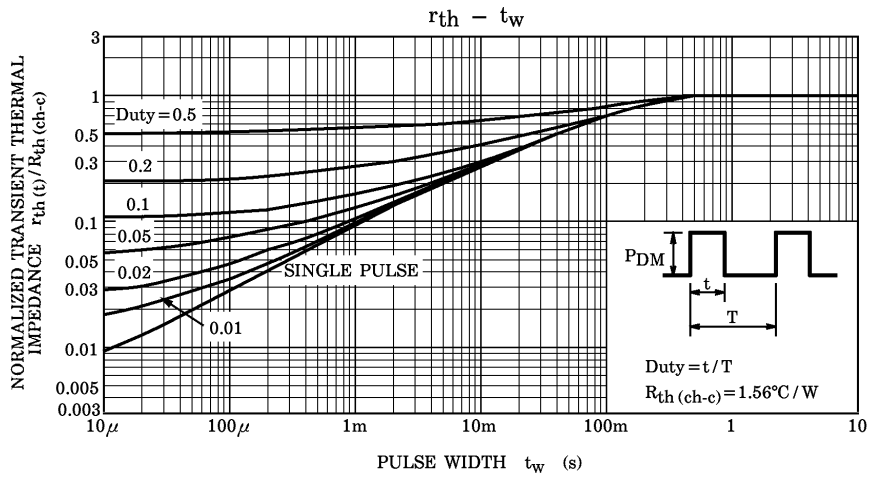
※ Lot Number

□ □ ← Month (Starting from Alphabet A)

— Year (Last Number of the Christian Era)







Peak $I_{AR} = 6A$, $R_G = 25\Omega$
 $V_{DD} = 90V$, $L = 16.8mH$

$$EAS = \frac{1}{2} \cdot L \cdot I^2 \cdot \left(\frac{BVDSS}{BVDSS - V_{DD}} \right)$$